

64 Mbit Mobile FCRAM™ 1.8 V, Burst Mode & Page Mode MB82DBS04164E-70L

■ FEATURES

- Pseudo SRAM with Single Data Rate (SDR) Burst Interface
- Complies with Common Specifications for Mobile RAM (COSMORAM) Revision 3
- 8 Words Page Read Access Capability
- Byte Control with \overline{LB} , \overline{UB} pin
- Low Power Consumption
- Various Power Down Mode
 - Sleep
 - 8 Mbit Partial
 - 16 Mbit Partial
 - 32 Mbit Partial
- Chip / Wafer Business
- 71pin Plastic FBGA Package for Engineering Sample only

■ MAIN SPECIFICATIONS

Part Number		MB82DBS04164E-70L
Organization		4 M WORD × 16 BIT
Supply Voltage		1.7 V to 1.95 V
Burst Frequency (Max.)	RL=7	104 MHz
CLK Access Time (Max.)	RL=6, 7	7 ns
Page Address Access Time (Max.)		20 ns
Address Access Time (Max.)		70 ns
Active Current (Max.)		40 mA
Standby Current (Max.)		200 μA
Power Down Current (Max.)	Sleep	10 μA

Note: FCRAM is a trademark of Fujitsu Limited, Japan.